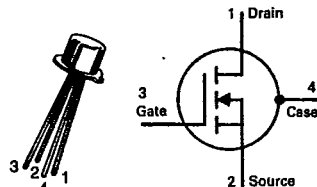


# 3N169 thru 3N171

CASE 20-03, STYLE 2  
TO-72 (TO-206AF)



## MOSFETs SWITCHING

N-CHANNEL — ENHANCEMENT

Refer to 2N4351 for graphs.

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	25	Vdc
Drain-Gate Voltage	$V_{DG}$	$\pm 35$	Vdc
Gate-Source Voltage	$V_{GS}$	$\pm 35$	Vdc
Drain Current	$I_D$	30	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 1.7	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	800 4.56	mW mW/ $^\circ\text{C}$
Junction Temperature Range	$T_J$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-65 to +175	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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#### OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ( $I_D = 10 \mu\text{Adc}$ , $V_{GS} = 0$ )	$V_{(BR)DSX}$	25	—	Vdc
Zero-Gate-Voltage Drain Current ( $V_{DS} = 10 \text{ Vdc}$ , $V_{GS} = 0$ ) ( $V_{DS} = 10 \text{ Vdc}$ , $V_{GS} = 0$ , $T_A = 125^\circ\text{C}$ )	$I_{DSS}$	— —	10 1.0	nAdc $\mu\text{Adc}$
Gate Reverse Current ( $V_{GS} = -35 \text{ Vdc}$ , $V_{DS} = 0$ ) ( $V_{GS} = -35 \text{ Vdc}$ , $V_{DS} = 0$ , $T_A = 125^\circ\text{C}$ )	$I_{GSS}$	— —	10 100	pAdc

#### ON CHARACTERISTICS

Gate Threshold Voltage ( $V_{DS} = 10 \text{ Vdc}$ , $I_D = 10 \mu\text{Adc}$ )	$V_{GS(Th)}$	3N169 3N170 3N171	0.5 1.0 1.5	1.5 2.0 3.0	Vdc
Drain-Source On-Voltage ( $I_D = 10 \text{ mAdc}$ , $V_{GS} = 10 \text{ Vdc}$ )	$V_{DS(on)}$		—	2.0	Vdc
On-State Drain Current ( $V_{GS} = 10 \text{ Vdc}$ , $V_{DS} = 10 \text{ Vdc}$ )	$I_{D(on)}$		10	—	mAdc

#### SMALL-SIGNAL CHARACTERISTICS

Drain-Source Resistance ( $V_{GS} = 10 \text{ Vdc}$ , $I_D = 0$ , $f = 1.0 \text{ kHz}$ )	$r_{ds(on)}$		—	200	Ohms
Forward Transfer Admittance ( $V_{DS} = 10 \text{ Vdc}$ , $I_D = 2.0 \text{ mAdc}$ , $f = 1.0 \text{ kHz}$ )	$ y_{fs} $		1000	—	$\mu\text{mhos}$
Input Capacitance ( $V_{DS} = 10 \text{ Vdc}$ , $V_{GS} = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{iss}$		—	5.0	pF
Reverse Transfer Capacitance ( $V_{DS} = 0$ , $V_{GS} = 0$ , $f = 1.0 \text{ MHz}$ )	$C_{rss}$		—	1.3	pF
Drain-Substrate Capacitance ( $V_{D(SUB)} = 10 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ )	$C_{d(sub)}$		—	5.0	pF

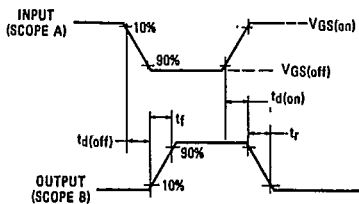
#### SWITCHING CHARACTERISTICS

Turn-On Delay Time	(VDD = 10 Vdc, $I_{D(on)} = 10 \text{ mAdc}$ , $V_{GS(on)} = 10 \text{ Vdc}$ , $V_{GS(off)} = 0$ , $R_G' = 50 \text{ Ohms}$ See Figure 1	$t_{d(on)}$	—	3.0	ns
Rise Time		$t_r$	—	10	ns
Turn-Off Delay Time		$t_{d(off)}$	—	3.0	ns
Fall Time		$t_f$	—	15	ns

T-3525

FIGURE 1 — SWITCHING TIME TEST CIRCUIT

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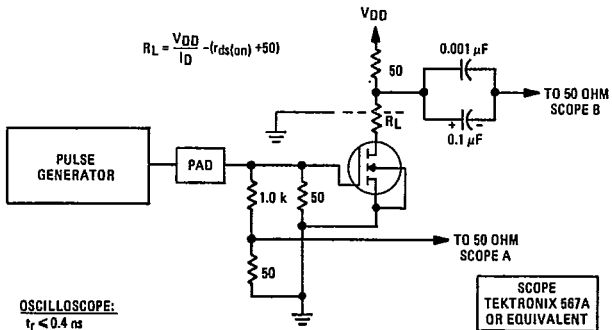
**INPUT PULSE:**

- $t_r < 0.33 \text{ ns}$
- $t_f < 0.33 \text{ ns}$
- $PW = 0.4 \mu\text{s}$
- Duty Cycle  $< 1.0\%$

**OSCILLOSCOPE:**

- $t_r < 0.4 \text{ ns}$
- $Z_{in} < 50 \text{ Ohms}$

$$R_L = \frac{V_{DD}}{I_D} - (r_{ds(on)} + 50)$$



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